4-Bit Dual-Supply **Non-Inverting Level Translator**

The NLSV4T244E is a 4-bit configurable dual-supply voltage level translator. The input A_n and output B_n ports are designed to track two different power supply rails, V_{CCA} and V_{CCB} respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input A_n to the output B_n port.

Features

- Wide V_{CCA} and V_{CCB} Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V_{CCA} and V_{CCB} Sequencing
- Outputs at 3-State until Active V_{CC} is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V_{CCB} at GND
- Data Rate > 200 Mbps @ $V_{CCA} = 1.8$ V, $V_{CCB} = 3.3$ V, $R_L = 2$ k Ω , $C_{L} = 15 \text{ pF}$
- Ultra-Small Packaging: 1.7 mm x 2.0 mm UQFN12
- These are Pb-Free Devices

Typical Applications

• Mobile Phones, PDAs, Other Portable Devices

Important Information

• ESD Protection for All Pins:

HBM (Human Body Model) > 2000 V MM (Machine Model) > 400 V



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MARKING DIAGRAMS



UQFN12 **MU SUFFIX** CASE 523AE



= Specific Device Code

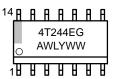
= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



SOIC-14 **D SUFFIX CASE 751A**





I WI

TSSOP-14 **DT SUFFIX CASE 948G**



Assembly Location

Wafer Lot Y, YY Year W. WW Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NLSV4T244EMUTAG	UQFN12 (Pb-Free)	3000/Tape & Reel
NLSV4T244EDR2G	SO-14 (Pb-Free)	2500/Tape & Reel
NLSV4T244EDTR2G	TSSOP14 (Pb-Free)	2500/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

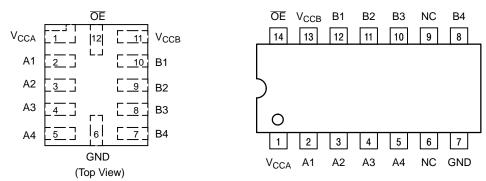


Figure 1. Pin Assignments

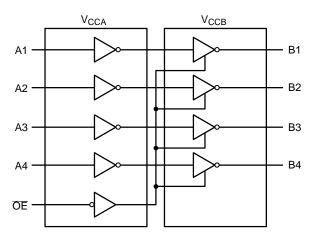


Figure 2. Logic Diagram

PIN ASSIGNMENT

PIN	FUNCTION
V _{CCA}	Input Port DC Power Supply
V _{CCB}	Output Port DC Power Supply
GND	Ground
A _n	Input Port
B _n	Output Port
ŌĒ	Output Enable

TRUTH TABLE

In	Outputs	
ŌĒ	A _n	B _n
L	L	L
L	Н	Н
Н	Х	3-State

MAXIMUM RATINGS

Symbol	Rating		Condition	Value	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage			-0.5 to +5.5	V
VI	DC Input Voltage	A _n		-0.5 to +5.5	V
V _C	Control Input	OE		-0.5 to +5.5	V
Vo	DC Output Voltage (Power Down)	B _n	$V_{CCA} = V_{CCB} = 0$	-0.5 to +5.5	V
	(Active Mode)	B _n		-0.5 to +5.5	V
	(Tri-State Mode)	B _n		-0.5 to +5.5	V
I _{IK}	DC Input Diode Current		V _I < GND	-20	mA
I _{OK}	DC Output Diode Current		V _O < GND	-50	mA
Io	DC Output Source/Sink Current			±50	mA
I _{CCA} , I _{CCB}	DC Supply Current Per Supply Pin			±100	mA
I _{GND}	DC Ground Current per Ground Pin			±100	mA
T _{STG}	Storage Temperature Range			-65 to +150	°C
TJ	Junction Temperature			+125	°C
$\theta_{\sf JA}$	Junction-to-Ambient Thermal Resistance			53	°C/W
$\Psi_{JC(top)}$	Junction-to-Case (Top) Thermal Resistance			10	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CCA} , V _{CCB}	Positive DC Supply Voltage		0.9	4.5	V
VI	Bus Input Voltage		GND	4.5	V
V _C	Control Input	ŌĒ	GND	4.5	V
V _{IO}	Bus Output Voltage (Power Down Mode)	B _n	GND	4.5	V
	(Active Mode)	B _n	GND	V _{CCB}	V
	(Tri-State Mode)	B _n	GND	4.5	V
T _A	Operating Temperature Range		-40	+85	°C
Δt / ΔV	Input Transition Rise or Rate V _I , from 30% to 70% of V _{CC} ; V _{CC} = 3.3 V \pm 0.3 V		0	10	nS

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

					−40°C to	o +85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Uni
V_{IH}	Input HIGH Voltage		3.6 – 4.5	0.9 - 4.5	2.2	_	V
	(An, \overline{OE})		2.7 – 3.6		2.0	_	
			2.3 – 2.7		1.6	_	
			1.4 – 2.3		0.65 * V _{CCA}	_	
			0.9 – 1.4		0.9 * V _{CCA}	_	
V_{IL}	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	-	0.8	V
	(An, $\overline{\text{OE}}$)		2.7 - 3.6		-	0.8	
			2.3 - 2.7		-	0.7	
			1.4 – 2.3		_	0.35 * V _{CCA}	
			0.9 – 1.4		-	0.1 * V _{CCA}	
V _{OH}	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IH}$	0.9 – 4.5	0.9 – 4.5	V _{CCB} - 0.2	_	V
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IH}$	0.9	0.9	0.75 * V _{CCB}	_	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	1.05	_	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.65	1.65	1.25	_	
			2.3	2.3	2.0	_	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	_	
			2.7	2.7	2.2	_	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	_	
			3.0	3.0	2.4	-	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	-	
V _{OL}	Output LOW Voltage	$I_{OL} = 100 \mu A; V_I = V_{IL}$	0.9 – 4.5	0.9 – 4.5	-	0.2	V
		$I_{OL} = 0.5 \text{ mA}; V_I = V_{IH}$	1.1	1.1	-	0.3	
		$I_{OL} = 2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	-	0.35	
		$I_{OL} = 6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	-	0.3	
		I_{OL} = 12 mA; V_I = V_{IL}	2.3	2.3	-	0.4	
			2.7	2.7	-	0.4	
		I_{OL} = 18 mA; V_I = V_{IL}	2.3	2.3	-	0.6	
			3.0	3.0	-	0.45	
		$I_{OL} = 24 \text{ mA}; V_I = V_{IL}$	3.0	3.0	-	0.6	
I _I	Input Leakage Current	$V_I = V_{CCA}$ or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μA
I _{OFF}	Power-Off Leakage Current	<u>OE</u> = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μA
I _{CCA}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μA
I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μA
CA + ICCB	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	4.0	μ.
ΔI_{CCA}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	_	10 5.0	μA
ΔI_{CCB}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μA
I _{OZ}	I/O Tri-State Output Leakage Current	$T_A = 25^{\circ}C$, $\overline{OE} = 0V_{CCA}$, $V_O = 0$ to $V_{CCB} + 0.5$ V	0.9 – 4.5	0.9 – 4.5	-	1.0	μA
		$T_A = 25$ °C, $\overline{OE} = 0V_{CCA}$, $V_O = 0$ to 4.5 V			_	75	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TOTAL STATIC POWER CONSUMPTION ($I_{CCA} + I_{CCB}$)

	-40°C to +85°C										
					V _{CCI}	_B (V)					
	4.	.5	3	.3	2.	.8	1.	.8	0.	.9	
V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

NOTE: Connect ground before applying supply voltage V_{CCA} or V_{CCB}. This device is designed with the feature that the power–up sequence of V_{CCA} and V_{CCB} will not damage the IC.

AC ELECTRICAL CHARACTERISTICS

							-40°C t	o +85°C					
							V _{CC}	_B (V)					
			4	.5	3	.3	2	.8	1	.8	1	.5	
Symbol	Parameter	V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation	4.5		3.0		3.2		3.4		3.7		4.0	nS
t _{PHL} (Note 1)	Delay,	3.6		3.3		3.5		3.7		4.0		4.3	
(Note 1)	A _n to B _n	2.8		3.5		3.7		3.9		4.2		4.5	
		1.8		3.8		4.0		4.2		4.5		4.8	
		1.5		4.1		4.3		4.5		4.8		5.0	
t _{PZH} ,	Output	4.5		4.4		4.8		5.2		5.7		6.2	nS
t _{PZL}	Enable,	3.3		4.7		5.1		5.5		6.0		6.5	
(Note 1)	OE to B _n	2.8		4.9		5.3		5.7		6.2		6.7	1
		1.8		5.2		5.6		6.0		6.5		7.0	
		1.5		5.5		5.9		6.3		6.8		7.3	
t _{PHZ} ,	Output	4.5		4.4		4.8		5.2		5.7		6.2	nS
t _{PLZ} (Note 1)	Disable,	3.3		4.7		5.1		5.5		6.0		6.5	
(Note 1)	OE to B _n	2.8		4.9		5.3		5.7		6.2		6.7	
		1.8		5.2		5.6		6.0		6.5		7.0	
		1.5		5.5		5.9		6.3		6.8		7.3	
t _{OSHL} ,	Output to	4.1		0.15		0.15		0.15		0.15		0.15	nS
toslh	l l)ata to ()ut-	3.6		0.15		0.15		0.15		0.15		0.15	
(Note 1)		2.8		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

^{1.} Propagation delays defined per Figures 3 and 4.

CAPACITANCE

Symbol	Parameter	Parameter Test Conditions			
C _{IN}	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF	
C _{I/O}	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF	
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	20	pF	

Typical values are at T_A = +25°C.
 C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC(operating)} ≅ C_{PD} x V_{CC} x f_{IN} x N_{SW} where I_{CC} = I_{CCA} + I_{CCB} and N_{SW} = total number of outputs switching.

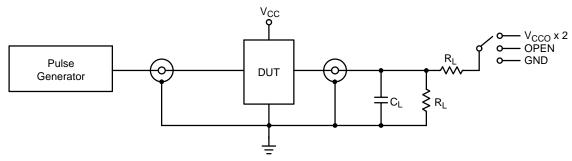


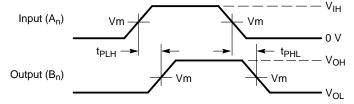
Figure 3. AC (Propagation Delay) Test Circuit

Test	Switch
t _{PLH} , t _{PHL}	OPEN
t _{PLZ} , t _{PZL}	V _{CCO} x 2
t _{PHZ} , t _{PZH}	GND

C_L = 15 pF or equivalent (includes probe and jig capacitance)

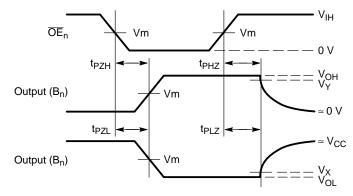
 $R_L = 2 k\Omega$ or equivalent

 Z_{OUT} of pulse generator = 50 Ω



Waveform 1 – Propagation Delays

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



Waveform 2 - Output Enable and Disable Times

 $t_R = t_F = 2.0 \ \text{ns}, \ 10\% \ \text{to} \ 90\%; \ f = 1 \ \text{MHz}; \ t_W = 500 \ \text{ns}$

Figure 4. AC (Propagation Delay) Test Circuit Waveforms

	V _{CC}							
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V			
V_{mA}	V _{CCA} /2							
V _{mB}	V _{CCB} /2							
V _X	V _{OL} x 0.1							
V _Y	V _{OH} x 0.9							

UQFN12 1.7x2.0, 0.4P CASE 523AE-01 **ISSUE A**



DATE 11 JUN 2007



PIN 1 REFERENCE

0.10 C

0.10 С

2X |

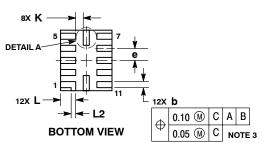




CONSTRUCTION

0.05 С 0.05 C 12X 🗀 **A1** SEATING PLANE **SIDE VIEW**

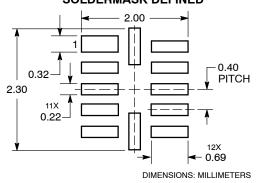
TOP VIEW



DETAIL B

-A B

MOUNTING FOOTPRINT SOLDERMASK DEFINED



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM
- FROM TERMINAL TIP.

 MOLD FLASH ALLOWED ON TERMINALS

 ALONG EDGE OF PACKAGE. FLASH 0.03

 MAX ON BOTTOM SURFACE OF
- TERMINALS.
 DETAIL A SHOWS OPTIONAL
 CONSTRUCTION FOR TERMINALS.

	MILLIN	IETERS						
DIM	MIN	MAX						
Α	0.45	0.55						
A1	0.00	0.05						
A3	0.127 REF							
b	0.15	0.25						
D	1.70 BSC							
Е	2.00	BSC						
е	0.40	BSC						
K	0.20							
L	0.45	0.55						
L1	0.00	0.03						
L2	0.15	REF						

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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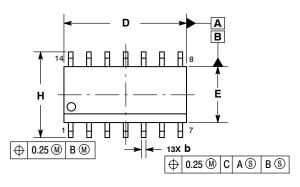
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△ 0.10

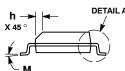
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





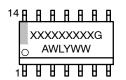




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7 °

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

C SEATING PLANE

STYLES ON PAGE 2

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

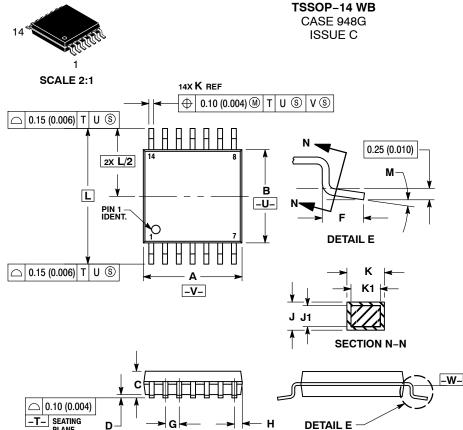
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY.
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8 °	0 °	8 °

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot ٧ = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

—	7.06
1	
	
	0.65
, <u> </u>	<u> </u>
14X	
0.36 14X 1.26	DIMENSIONS: MILLIMETERS

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